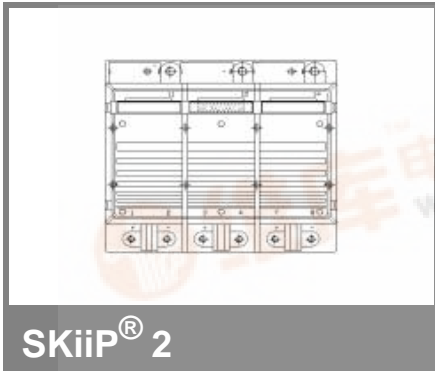


# SKiiP 792GB170-3D



## 2-pack - integrated intelligent Power System

### Power section

#### SKiiP 792GB170-3D

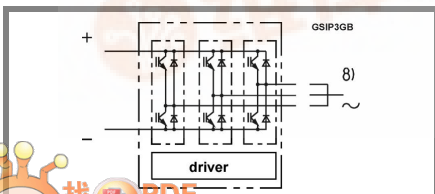
### Features

- SKiiP technology inside
- CAL diode technology
- Integrated current sensor
- Integrated temperature sensor
- Integrated heat sink
- IEC 60721-3-3 (humidity) class 3K3/IE32 (SKiiP® 2 System)
- IEC 60068-1 (climate) 40/125/56
- UL recognized file no. E63532

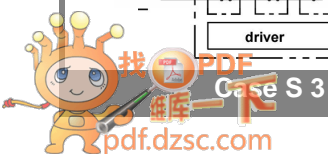
- 1) with assembly of suitable MKP capacitor per terminal (SEMIKRON type is recommended)
- 8) AC connection busbars must be connected by the user; copper busbars available on request

Absolute Maximum Ratings		$T_s = 25^\circ\text{C}$ unless otherwise specified	
Symbol	Conditions	Values	Units
<b>IGBT</b>			
$V_{CES}$	Operating DC link voltage	1700	V
$V_{CC}^{1)}$		1200	V
$V_{GES}$		$\pm 20$	V
$I_C$	$T_s = 25 (70)^\circ\text{C}$	750 (562)	A
<b>Inverse diode</b>			
$I_F = -I_C$	$T_s = 25 (70)^\circ\text{C}$	750 (562)	A
$I_{FSM}$	$T_j = 150^\circ\text{C}$ , $t_p = 10\text{ ms}$ ; sin.	6480	A
$I^2t$ (Diode)	Diode, $T_j = 150^\circ\text{C}$ , 10 ms	210	$\text{kA}^2\text{s}$
$T_j$ , ( $T_{stg}$ )		- 40 (- 25) ... + 150 (125)	$^\circ\text{C}$
$V_{isol}$	AC, 1 min. (mainterminals to heat sink)	4000	V

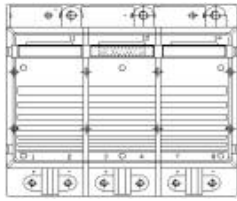
Characteristics		$T_s = 25^\circ\text{C}$ unless otherwise specified						
Symbol	Conditions	min.	typ.	max.	Units			
<b>IGBT</b>								
$V_{CESat}$	$I_C = 600\text{ A}$ , $T_j = 25 (125)^\circ\text{C}$		3,3 (4,3)	3,9	V			
$V_{CEO}$	$T_j = 25 (125)^\circ\text{C}$		1,7 (2)	2 (2,3)	V			
$r_{CE}$	$T_j = 25 (125)^\circ\text{C}$		2,7 (3,9)	3,2 (4,4)	$\text{m}\Omega$			
$I_{CES}$	$V_{GE} = 0\text{ V}$ , $V_{CE} = V_{CES}$ , $T_j = 25 (125)^\circ\text{C}$		(45)	3	$\text{mA}$			
$E_{on} + E_{off}$	$I_C = 600\text{ A}$ , $V_{CC} = 900\text{ V}$ $T_j = 125^\circ\text{C}$ , $V_{CC} = 1200\text{ V}$			518 763	$\text{mJ}$ $\text{mJ}$			
$R_{CC'} + EE'$	terminal chip, $T_j = 125^\circ\text{C}$		0,17		$\text{m}\Omega$			
$L_{CE}$	top, bottom		5		$\text{nH}$			
$C_{CHC}$	per phase, AC-side		2,4		$\text{nF}$			
<b>Inverse diode</b>								
$V_F = V_{EC}$	$I_F = 600\text{ A}$ , $T_j = 25 (125)^\circ\text{C}$		2,3 (2,1)	2,9	V			
$V_{TO}$	$T_j = 25 (125)^\circ\text{C}$		1,3 (1)	1,6 (1,3)	V			
$r_T$	$T_j = 25 (125)^\circ\text{C}$		1,7 (1,9)	2,1 (2,3)	$\text{m}\Omega$			
$E_{rr}$	$I_C = 600\text{ A}$ , $V_{CC} = 900\text{ V}$ $T_j = 125^\circ\text{C}$ , $V_{CC} = 1200\text{ V}$			64 75	$\text{mJ}$ $\text{mJ}$			
<b>Mechanical data</b>								
$M_{dc}$	DC terminals, SI Units	6		8	$\text{Nm}$			
$M_{ac}$	AC terminals, SI Units	13		15	$\text{Nm}$			
w	SKiiP® 2 System w/o heat sink		2,7		kg			
w	heat sink		6,6		kg			
<b>Thermal characteristics (P16 heat sink; 295<math>\text{m}^3/\text{h}</math>); "r" reference to temperature sensor</b>								
$R_{th(j-s)I}$	per IGBT			0,027	$\text{K/W}$			
$R_{th(j-s)D}$	per diode			0,089	$\text{K/W}$			
$R_{th(s-a)}$	per module			0,036	$\text{K/W}$			
$Z_{th}$	$R_i$ ( $\text{mK/W}$ ) (max. values)			$\tau_{th}(s)$				
	1	2	3	4	1	2	3	4
$Z_{th(j-r)I}$					1	0,13	0,001	1
$Z_{th(j-r)D}$					1	0,13	0,001	1
$Z_{th(r-a)}$					204	60	6	0,02



This technical information specifies semiconductor devices but promises no characteristics. No warranty or guarantee, expressed or implied is made regarding delivery, performance or suitability.



# SKiiP 792GB170-3D



SKiiP<sup>®</sup> 2

## 2-pack - integrated intelligent Power System

### 2-pack integrated gate driver

#### SKiiP 792GB170-3D

#### Gate driver features

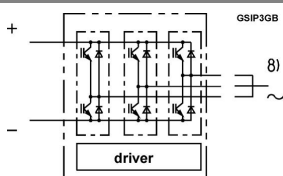
- CMOS compatible inputs
- Wide range power supply
- Integrated circuitry to sense phase current, heat sink temperature and DC-bus voltage (option)
- Short circuit protection
- Over current protection
- Over voltage protection (option)
- Power supply protected against under voltage
- Interlock of top/bottom switch
- Isolation by transformers
- Fibre optic interface (option for GB-types only)
- IEC 60068-1 (climate) 25/85/56

Absolute Maximum Ratings		$T_a = 25\text{ }^\circ\text{C}$ unless otherwise specified	
Symbol	Conditions	Values	Units
$V_{S1}$	stabilized 15 V power supply	18	V
$V_{S2}$	unstabilized 24 V power supply	30	V
$V_{iH}$	input signal voltage (high)	15 + 0,3	V
dv/dt	secondary to primary side	75	kV/ $\mu$ s
$V_{isol1O}$	input / output (AC, r.m.s., 2s )	4000	Vac
$V_{isol12}$	output 1 / output 2 (AC, r.m.s., 2s )	1500	Vac
$f_{sw}$	switching frequency	11	kHz
$f_{out}$	output frequency for $I=I_C$ ; sin.	1	kHz
$T_{op}$ ( $T_{stg}$ )	operating / storage temperature	- 40 ... + 85	$^\circ\text{C}$

Characteristics		$(T_a = 25\text{ }^\circ\text{C})$			
Symbol	Conditions	min.	typ.	max.	Units
$V_{S1}$	supply voltage stabilized	14,4	15	15,6	V
$V_{S2}$	supply voltage non stabilized	20	24	30	V
$I_{S1}$	$V_{S1} = 15\text{ V}$	$260+500 \cdot f/f_{max} + 1,2 \cdot (I_{AC}/A)$			mA
$I_{S2}$	$V_{S2} = 24\text{ V}$	$200+370 \cdot f/f_{max} + 0,85 \cdot (I_{AC}/A)$			mA
$V_{iT+}$	input threshold voltage (High)	12,3			V
$V_{iT-}$	input threshold voltage (Low)	4,6			V
$R_{IN}$	input resistance	10			k $\Omega$
$t_{d(on)O}$	input-output turn-on propagation time	1,5			$\mu$ s
$t_{d(off)O}$	input-output turn-off propagation time	1,4			$\mu$ s
$t_{pERRRESET}$	error memory reset time	9			$\mu$ s
$t_{TD}$	top / bottom switch : interlock time	3,3			$\mu$ s
$I_{analogOUT}$	8 V corresponds to max. current of 15 V supply voltage (available when supplied with 24 V)	750			A
$I_{Vs1outmax}$	output current at pin 12/14	50			mA
$I_{A0max}$	output current at pin 12/14	5			mA
$V_{O1}$	logic low output voltage	0,6			V
$V_{O1H}$	logic high output voltage	30			V
$I_{TRIPSC}$	over current trip level ( $I_{analog OUT} = 10\text{ V}$ )	938			A
$I_{TRIPLG}$	ground fault protection	120			A
$T_{tp}$	over temperature protection	110			$^\circ\text{C}$
$U_{DCTRIP}$	trip level of $U_{DC}$ -protection ( $U_{analog OUT} = 9\text{ V}$ ); (option)	1200			V

For electrical and thermal design support please use SEMISEL.  
Access to SEMISEL is via SEMIKRON website <http://www.semikron.com>.

This technical information specifies semiconductor devices but promises no characteristics. No warranty or guarantee, expressed or implied is made regarding delivery, performance or suitability.



Case S 3